

Supplementary information for:

## **Condenson-related thermoelectric properties and formation of coherent nanoinclusions in Te-substituted In<sub>4</sub>Se<sub>3</sub>**

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Table S1. EDS point analysis results at five arbitrary points from the matrix and from the nanoinclusions in  $\text{In}_4(\text{Se}_{0.95}\text{Te}_{0.05})_{2.6}$  compound.

Point analysis	Matrix			Nanoinclusion		
	In (wt%)	Se (wt%)	Te (wt%)	In (wt%)	Se (wt%)	Te (wt%)
#1	69.84	28.52	1.64	85.11	14.35	0.54
#2	71.42	26.83	1.75	77.05	22.42	0.54
#3	68.68	29.25	2.07	75.79	24.39	-0.18
#4	69.41	29.36	1.23	78.65	23.60	-2.24
#5	69.97	28.48	1.54	80.39	19.43	0.18
Average	69.90	28.50	1.60	79.40	20.80	-0.20

Table S2. EDS point analysis results at five arbitrary points from the matrix and from the nanoinclusions in  $\text{In}_4\text{Se}_{2.6}$  compound.

Point analysis	Matrix		Nanoinclusion	
	In (wt%)	Se (wt%)	In (wt%)	Se (wt%)
#1	69.29	30.71	71.50	23.50
#2	70.99	29.01	83.16	16.84
#3	66.28	33.72	72.29	27.71
#4	70.25	29.75	75.01	24.99
#5	72.31	27.69	81.69	18.31
Average	69.80	30.20	76.70	23.30

Figure S1. A HRTEM micrograph of cation-substituted  $(\text{In}_{0.98}\text{Sn}_{0.02})_4\text{Se}_{2.6}$  compound along  $\langle 001 \rangle$  zone axis.

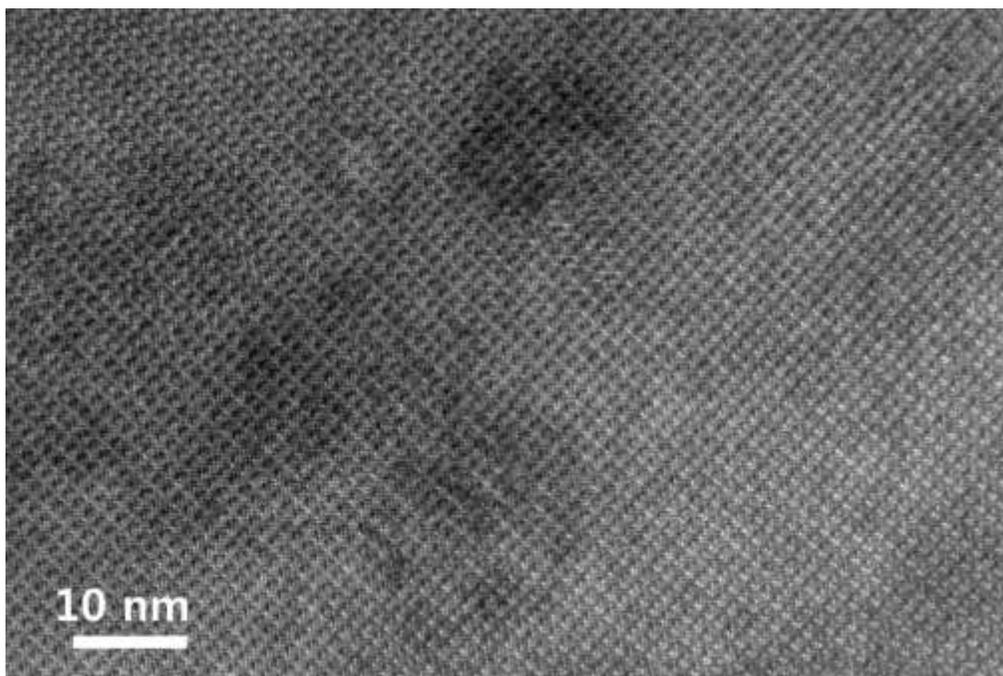


Figure S2. XRD patterns of unalloyed  $\text{In}_4\text{Se}_{2.6}$  and Te-substituted  $\text{In}_4\text{Se}_{3-\delta}$  (IST) compounds. Although a tiny amount of metallic indium was detected, all samples were mostly composed of  $\text{In}_4\text{Se}_3$  phase. However, no extra XRD peak originating from the nanoinclusion could be observed in the XRD patterns.

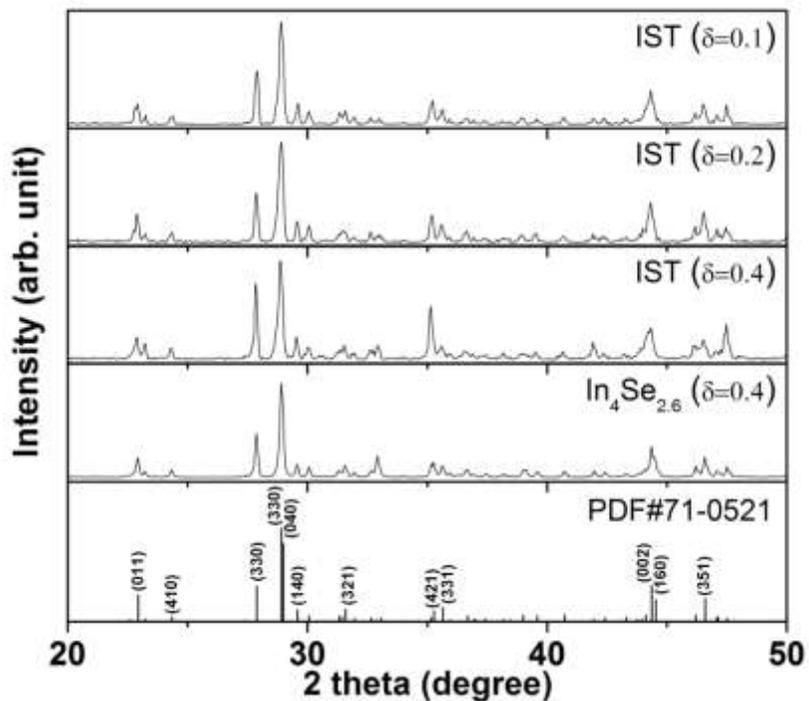


Figure S3. A SEM micrograph of a fractured surface of unalloyed  $\text{In}_4\text{Se}_{2.6}$  compound.

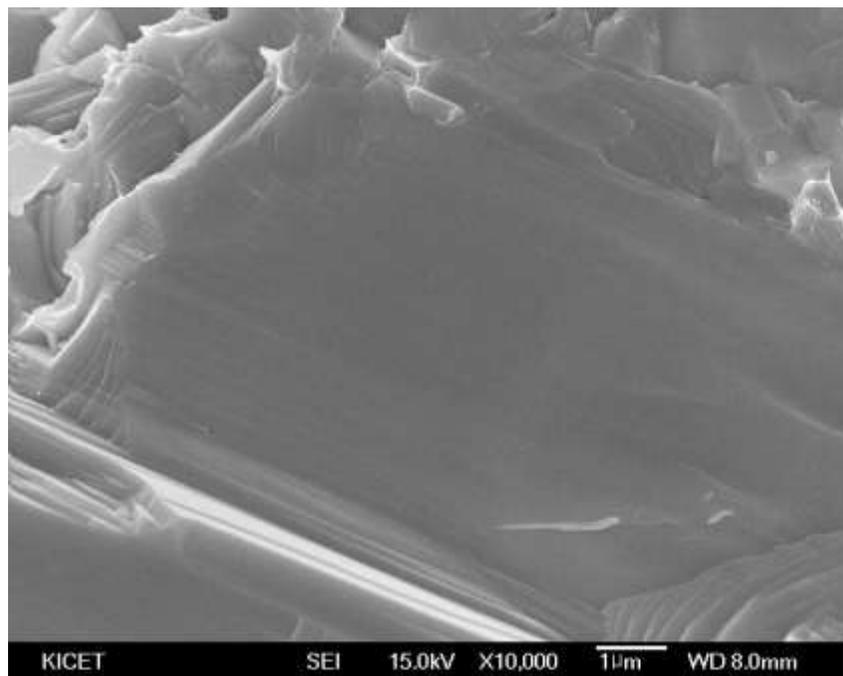


Figure S4. (a) A low-magnification bright-field TEM micrograph of unalloyed  $\text{In}_4\text{Se}_{2.6}$ . (b) and (c) are enlarged bright-field TEM micrographs of Grain A and B, respectively. In these figures, the wide distribution of the nano-inclusions can be clearly observed.

